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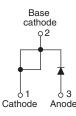
Vishay Semiconductors

Hyperfast Rectifier, 8 A FRED Pt[®]



TO-220 FULL-PAK

TO-220AC





VS-8ETH06PbF VS-8ETH06-N3

VS-8ETH06FPPbF VS-8ETH06FP-N3

PRODUCT SUMMARY								
Package	TO-220AC, TO-220FP							
I _{F(AV)}	8 A							
V _R	600 V							
V _F at I _F	1.3 V							
t _{rr} typ.	18 ns							
T _J max.	175 °C							
Diode variation	Single die							

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Repetitive peak reverse voltage	V _{RRM}		600	V					
Average rectified forward current		T _C = 144 °C	- 8						
FULL-P/	AK I _{F(AV)}	T _C = 108 °C	0						
Non-repetitive peak surge current		T _J = 25 °C	90	А					
FULL-P	AK IFSM		100						
Repetitive peak forward current	I _{FM}		16						
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-				
Forward voltage	V _F	I _F = 8 A	-	2.0	2.4	V			
		I _F = 8 A, T _J = 150 °C	-	1.3	1.8				
Deverse leekerse eurrent	I _R	$V_{R} = V_{R}$ rated	-	0.3	50				
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	55	500	μA			
Junction capacitance	CT	V _R = 600 V	-	17	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

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RoHS

COMPLIANT

HALOGEN

FREE

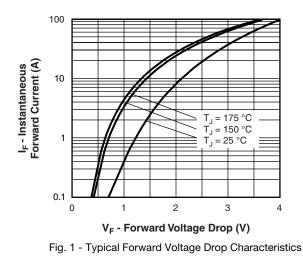
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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 \text{ A}, \ dI_F/dt = 100$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$			22				
Reverse recovery time	+	$I_F = 8 \text{ A}, dI_F/dt = 100$	-	20	25	ns				
neverse recovery time	t _{rr}	T _J = 25 °C		-	25	-	115			
		T _J = 125 °C	I _F = 8 A dI _F /dt = 200 A/µs V _B = 390 V	-	40	-				
Poak rocovary ourrant	I _{RRM}	T _J = 25 °C		-	2.4	-	A			
Peak recovery current		T _J = 125 °C		-	4.8	-				
Poverse recevery charge	Q _{rr}	T _J = 25 °C		-	25	-	nC			
Reverse recovery charge		T _J = 125 °C		-	120	-				
Reverse recovery time	t _{rr}		I _F = 8 A	-	33	-	ns			
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 600 A/µs	-	12	-	А			
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	220	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance,	R _{thJC}		-	1.4	2				
junction to case (FULL-PAK)	nthJC		-	3.4	4.3				
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Waiaht			-	2.0	-	g			
Weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking davias		Case style TO-220AC 8ET		H06					
Marking device		Case style TO-220 FULL-PAK		8ETH	106FP				



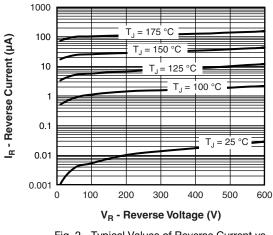


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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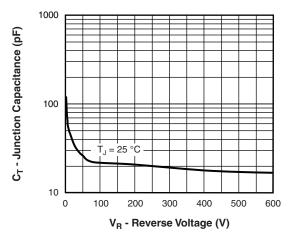


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

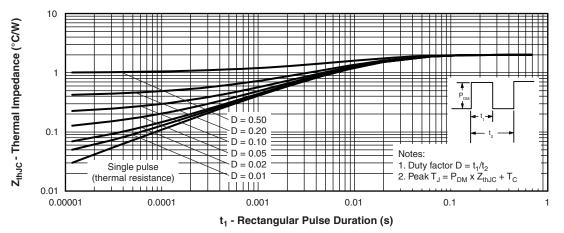


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

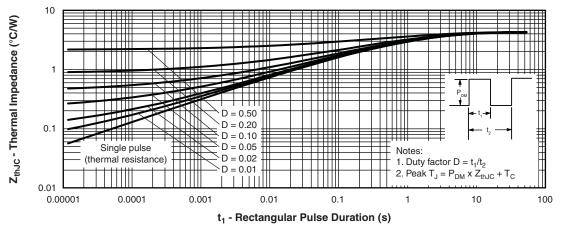
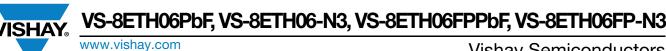
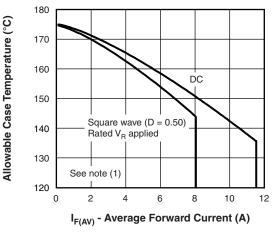


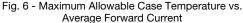
Fig. 5 - Maximum Thermal Impedance ZthJC Characteristics (FULL-PAK)

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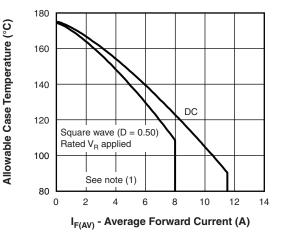
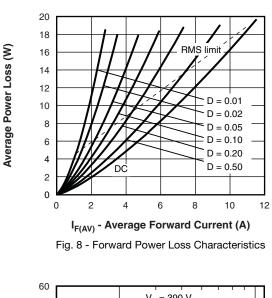
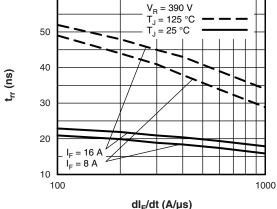
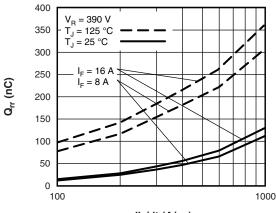


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)









dl_F/dt (A/µs) Fig. 10 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ 8); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \\ \end{array}$

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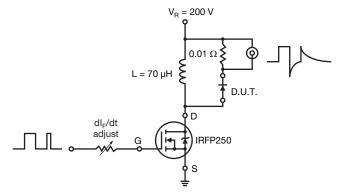
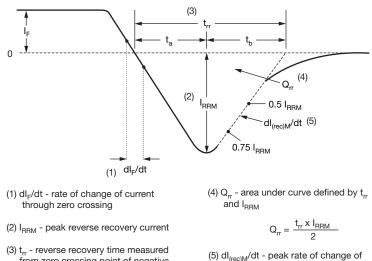


Fig. 11 - Reverse Recovery Parameter Test Circuit



(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

Fig. 12 - Reverse Recovery Waveform and Definitions

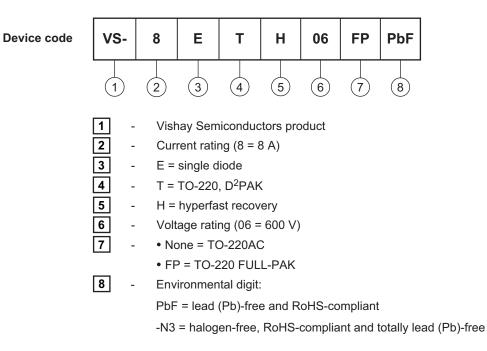
current during t_b portion of t_{rr}

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ORDERING INFORMATION TABLE

VISHA



ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-8ETH06PbF	50	1000	Antistatic plastic tube						
VS-8ETH06-N3	50	1000	Antistatic plastic tube						
VS-8ETH06FPPbF	50	1000	Antistatic plastic tube						
VS-8ETH06FP-N3	50	1000	Antistatic plastic tube						

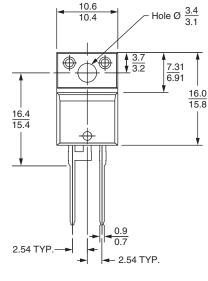
LINKS TO RELATED DOCUMENTS							
Dimensions -	TO-220AC	www.vishay.com/doc?95221					
Dimensions	TO-220FP	www.vishay.com/doc?95005					
	TO-220ACPbF	www.vishay.com/doc?95224					
Part marking information	TO-220AC-N3	www.vishay.com/doc?95068					
Fart marking mormation	TO-220FPPbF	www.vishay.com/doc?95009					
	TO-220FP-N3	www.vishay.com/doc?95440					



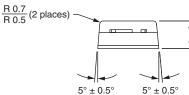
Outline Dimensions

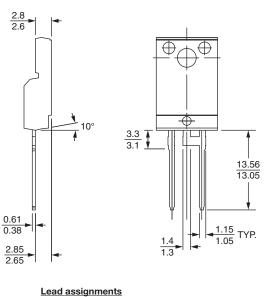
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DIMENSIONS in millimeters



 $\frac{4.8}{4.6}$





<u>Lead assignments</u> <u>Diodes</u> 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



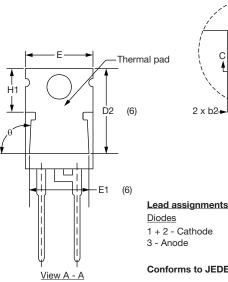
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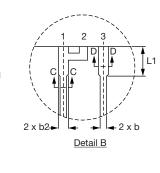
TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

⊕ 0.015 **()** BA()

SYMBOL	MILLIN	IETERS	INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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